

# DATA SHEET

**BFT92**

**PNP 5 GHz wideband transistor**

Product specification  
File under Discrete Semiconductors, SC14

November 1992

## PNP 5 GHz wideband transistor

## BFT92

## DESCRIPTION

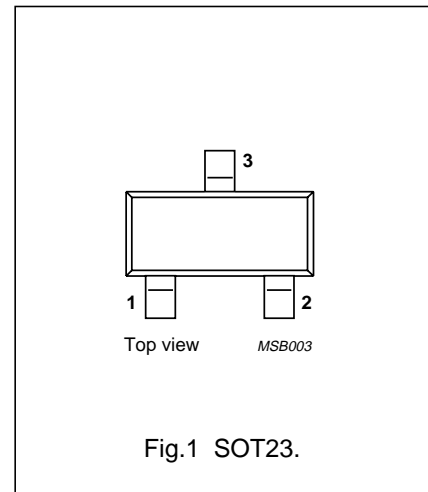
PNP transistor in a plastic SOT23 envelope.

It is primarily intended for use in RF wideband amplifiers, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analyzers, etc. The transistor features low intermodulation distortion and high power gain; due to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

NPN complements are BFR92 and BFR92A.

## PINNING

PIN	DESCRIPTION
Code: W1p	
1	base
2	emitter
3	collector



## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–15	V
$I_C$	DC collector current		–	–25	mA
$P_{tot}$	total power dissipation	up to $T_s = 95\text{ °C}$ ; note 1	–	300	mW
$f_T$	transition frequency	$I_C = -14\text{ mA}$ ; $V_{CE} = -10\text{ V}$ ; $f = 500\text{ MHz}$	5	–	GHz
$C_{re}$	feedback capacitance	$I_C = -2\text{ mA}$ ; $V_{CE} = -10\text{ V}$ ; $f = 1\text{ MHz}$	0.7	–	pF
$G_{UM}$	maximum unilateral power gain	$I_C = -14\text{ mA}$ ; $V_{CE} = -10\text{ V}$ ; $f = 500\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	18	–	dB
F	noise figure	$I_C = -5\text{ mA}$ ; $V_{CE} = -10\text{ V}$ ; $f = 500\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	2.5	–	dB
$d_{im}$	intermodulation distortion	$I_C = -14\text{ mA}$ ; $V_{CE} = -10\text{ V}$ ; $R_L = 75\text{ }\Omega$ ; $V_o = 150\text{ mV}$ ; $T_{amb} = 25\text{ °C}$ ; $f_{(p+q-r)} = 493.25\text{ MHz}$	–60	–	dB

## Note

- $T_s$  is the temperature at the soldering point of the collector tab.

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**LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–15	V
$V_{EBO}$	emitter-base voltage	open collector	–	–2	V
$I_C$	DC collector current		–	–25	mA
$I_{CM}$	peak collector current	$f > 1$ MHz	–	–35	mA
$P_{tot}$	total power dissipation	up to $T_s = 95$ °C; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	150	°C
$T_j$	junction temperature		–	175	°C

**THERMAL RESISTANCE**

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 95$ °C; note 1	260 K/W

**Note**

- $T_s$  is the temperature at the soldering point of the collector tab.

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**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -10\text{ V};$	–	–	–50	nA
$h_{FE}$	DC current gain	$I_C = -14\text{ mA}; V_{CE} = -10\text{ V}$	20	50	–	
$f_T$	transition frequency	$I_C = -14\text{ mA}; V_{CE} = -10\text{ V};$ $f = 500\text{ MHz}$	–	5	–	GHz
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	0.75	–	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{EB} = -0.5\text{ V}; f = 1\text{ MHz}$	–	0.8	–	pF
$C_{re}$	feedback capacitance	$I_C = -2\text{ mA}; V_{CE} = -10\text{ V}; f = 1\text{ MHz}$	–	0.7	–	pF
$G_{UM}$	maximum unilateral power gain (note 1)	$I_C = -14\text{ mA}; V_{CE} = -10\text{ V};$ $f = 500\text{ MHz}; T_{amb} = 25\text{ °C}$	–	18	–	dB
F	noise figure	$I_C = -5\text{ mA}; V_{CE} = -10\text{ V};$ $f = 500\text{ MHz}; T_{amb} = 25\text{ °C}$	–	2.5	–	dB
$V_o$	output voltage	note 2	–	150	–	mV

**Notes**

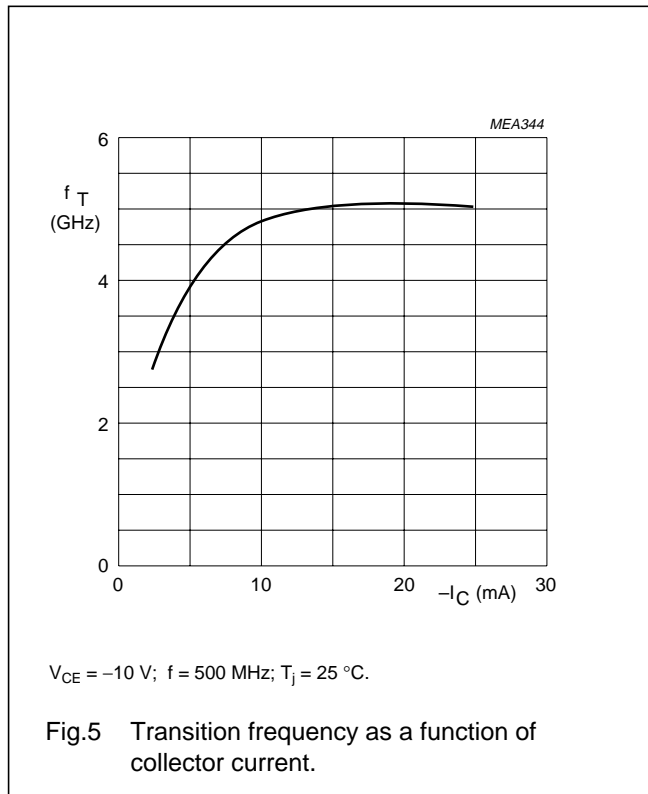
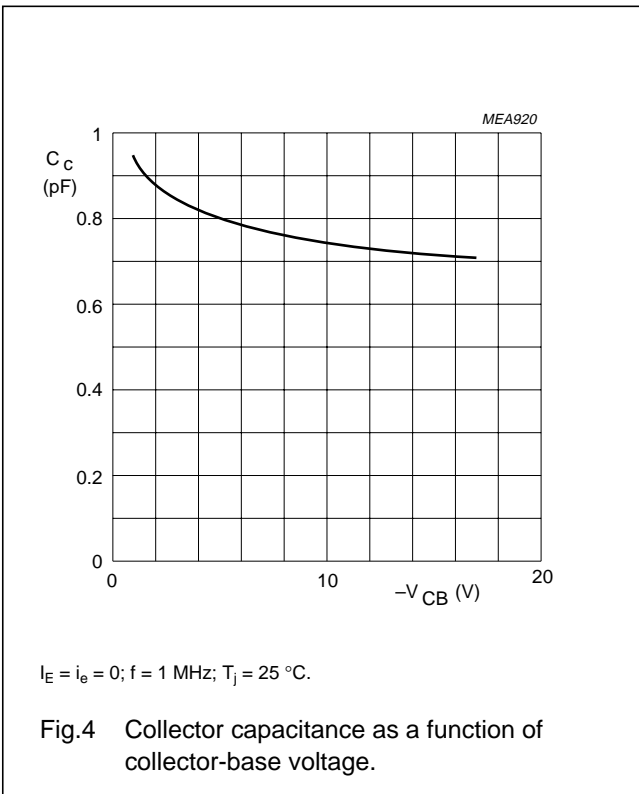
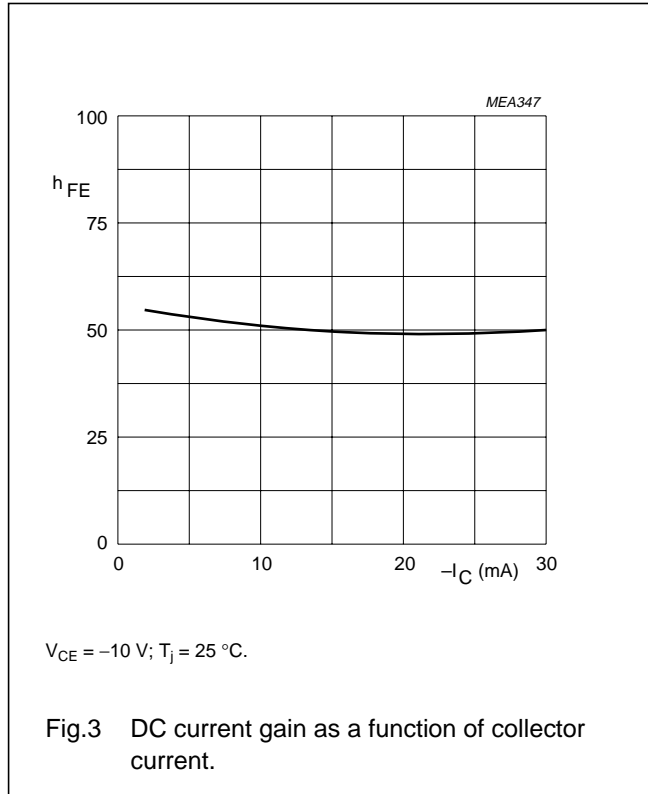
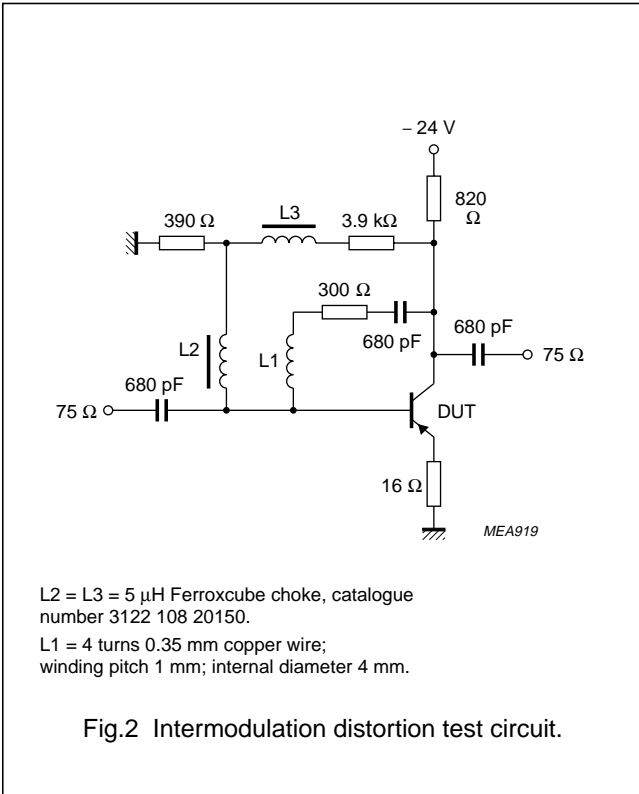
1.  $G_{UM}$  is the maximum unilateral power gain, assuming  $S_{12}$  is zero and

$$G_{UM} = 10 \log \left( \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \right) \text{dB.}$$

2.  $d_{im} = -60\text{ dB}$  (DIN 45004B);  $I_C = -14\text{ mA}; V_{CE} = -10\text{ V}; R_L = 75\ \Omega;$   
 $V_p = V_o$  at  $d_{im} = -60\text{ dB}; f_p = 495.25\text{ MHz};$   
 $V_q = V_o - 6\text{ dB}; f_q = 503.25\text{ MHz};$   
 $V_r = V_o - 6\text{ dB}; f_r = 505.25\text{ MHz};$   
 measured at  $f_{(p+q-r)} = 493.25\text{ MHz}.$

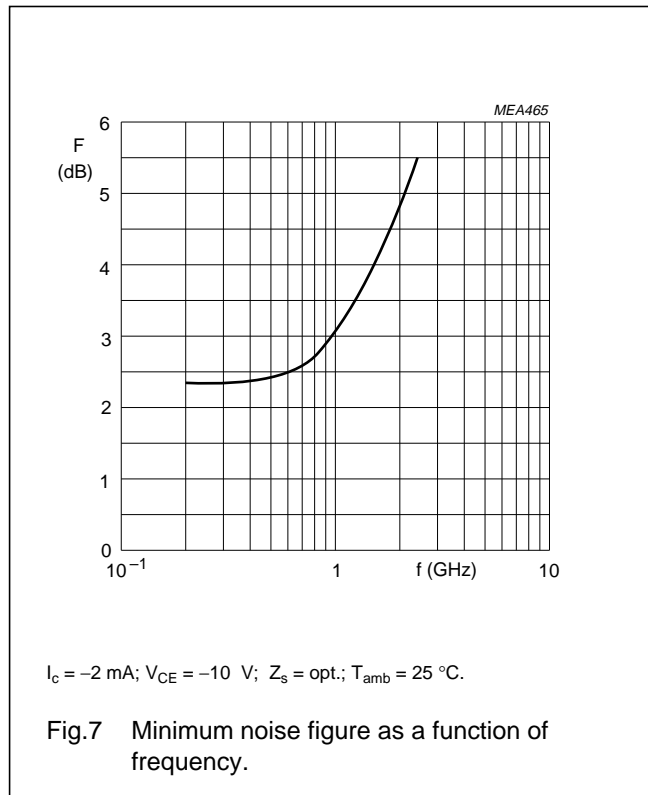
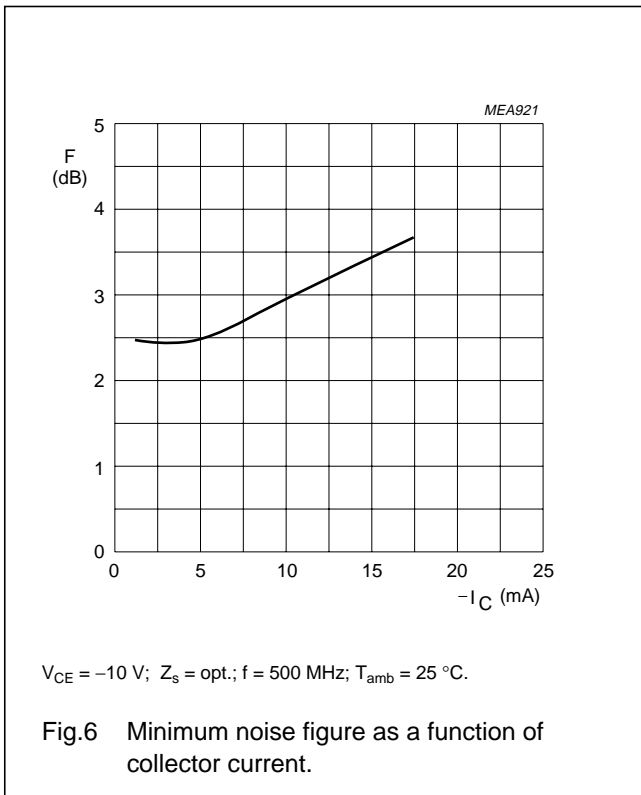
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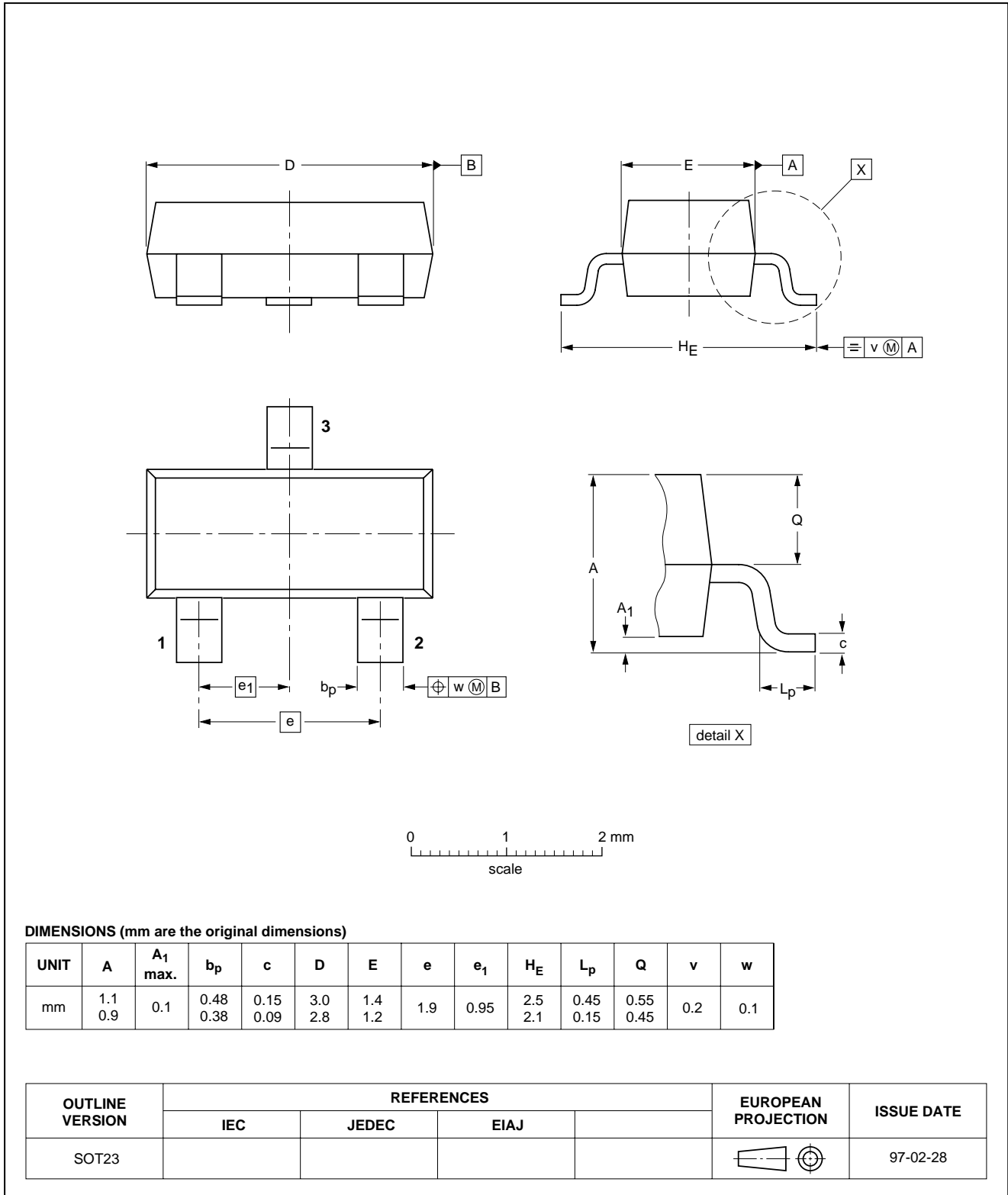
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

**LIFE SUPPORT APPLICATIONS**

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